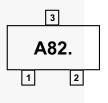
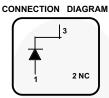
May 2016



# BAS21 General-Purpose High Voltage Diode







### **Ordering Information**

Part Number	Top Mark	Package	Packing Method
BAS21	A82.	SOT-23 3L	Tape and Reel

### Absolute Maximum Ratings<sup>(1), (2)</sup>

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter		Value	Unit
W <sub>IV</sub>	Working Inverse Voltage		250	V
I <sub>O</sub>	Average Rectified Current		200	mA
١ <sub>F</sub>	DC Forward Current		600	mA
i <sub>f</sub>	Recurrent Peak Forward Current		700	mA
i <sub>f(surge)</sub>	Peak Forward Surge Current	Pulse Width = 1.0 second	1.0	Α
		Pulse Width = 1.0 microsecond	2.0	
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C
TJ	Operating Junction Temperature		150	°C

#### Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

## **Thermal Characteristics**

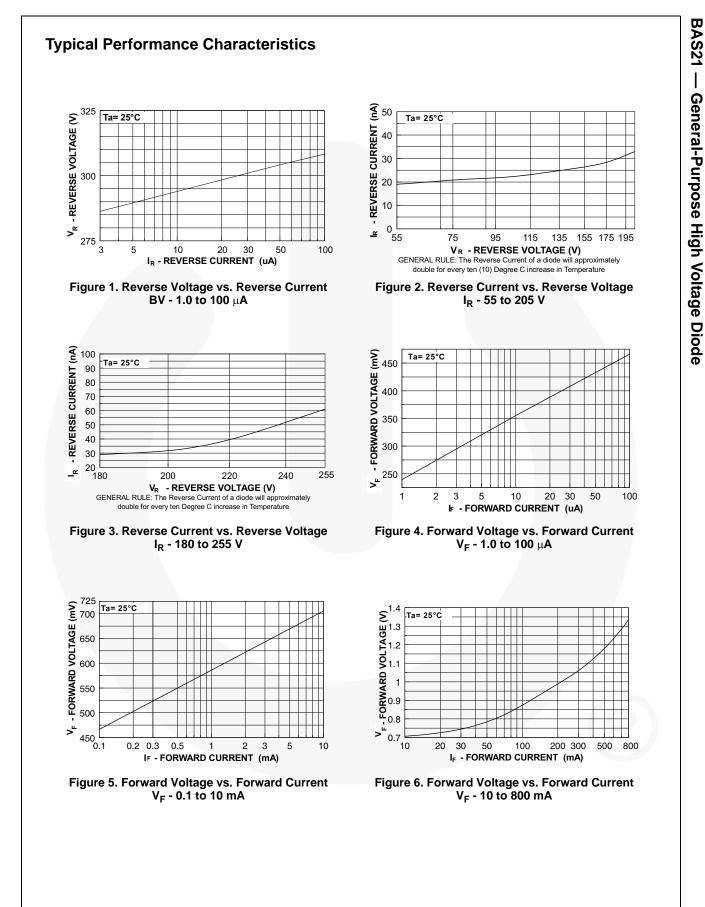
Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

Symbol	Parameter	Max.	Unit
PD	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/°C
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

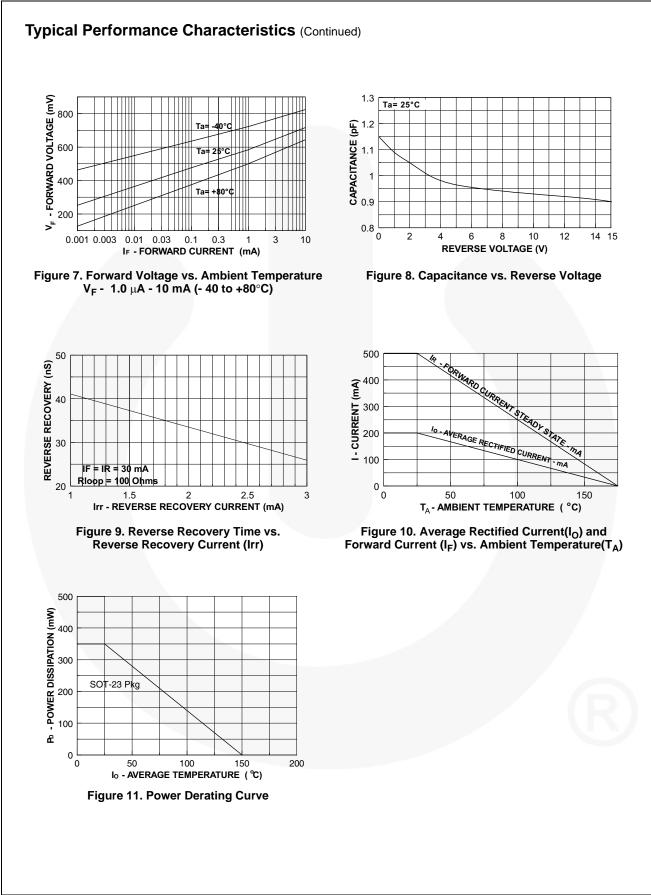
### **Electrical Characteristics**

Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

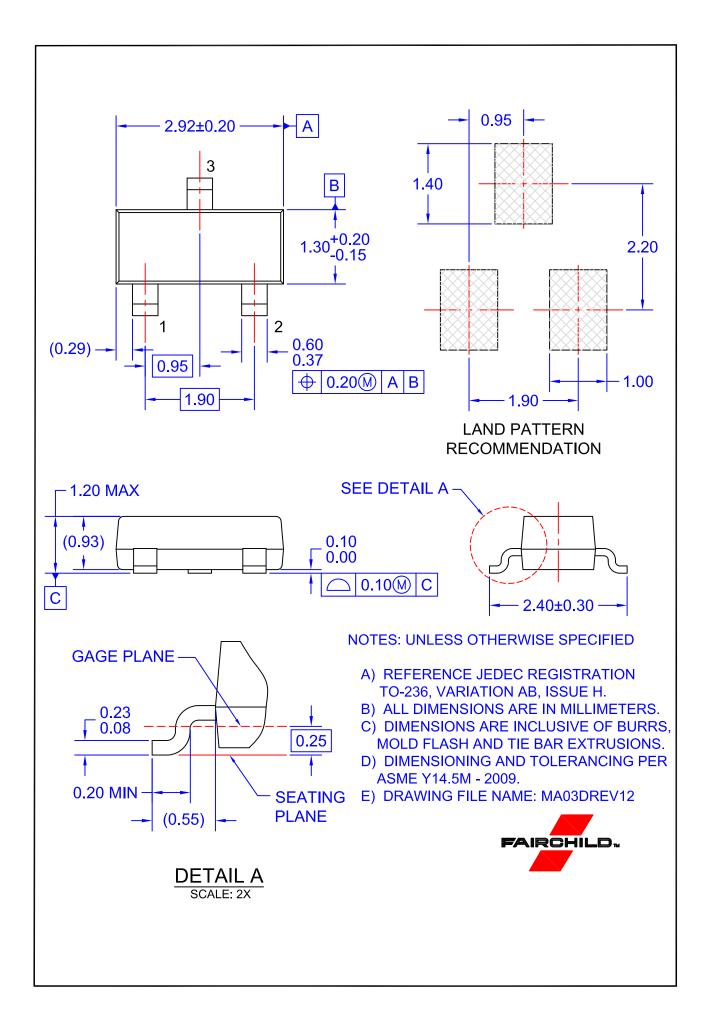
Symbol	Parameter	Conditions	Min.	Max.	Unit
B <sub>V</sub>	Breakdown Voltage	I <sub>R</sub> = 100 μA	250		V
I <sub>R</sub>	Reverse Voltage Leakage Current	V <sub>R</sub> = 200 V		100	nA
		V <sub>R</sub> = 200 V, T <sub>A</sub> = 150°C		100	μΑ
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 100 mA		1.0	V
		I <sub>F</sub> = 200 mA		1.25	V
CO	Diode Capacitance	V <sub>R</sub> = 0, f = 1.0 MHz		5.0	pF
T <sub>RR</sub>	Reverse Recovery Time	$I_{F} = I_{R} = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_{L} = 100 \Omega$		50	nS



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BAS21 — General-Purpose High Voltage Diode



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